



**SW Test Workshop**  
Semiconductor Wafer Test Workshop

# Interlayer Dielectric (ILD) Cracking Mechanisms and their Effects on Probe Processes



**Daniel Stillman, Daniel  
Fresquez**

Texas Instruments Inc.

June 5-8, 2016

# Outline

- **Probe Optimization – Why is it needed?**
- **Objective and obstacles**
- **Thermal Challenges**
  - Interface movement
  - Affects on Z and pre-set OT
- **Implementing an automated solution**
- **Improvements in Silicon Design**
- **Acknowledgments**

# Speed Optimization – Why is it needed?

- **Improve quality for our customers**
  - Extreme temperatures, multiple insertions, and automotive quality requirements make card technology selection critical for the end product.
- **Provide a means for PC design**
  - Complex probe card designs (matrix, skip row / skip column, diagonal) call for more upfront design work to insure optimal efficiency.
- **Provide robust design rules for future technology nodes**
  - How do we design for probe?

## Objective

- **Challenge:** Changes in metal design can results in cracks in barrier metals and insulation layers. These cracks can results in metal migration and functional failures
- **Obstacles:** Slowing down Z-speed reduces force induced by probe card technology on IC devices, thus preventing di-electric crack fail modes.



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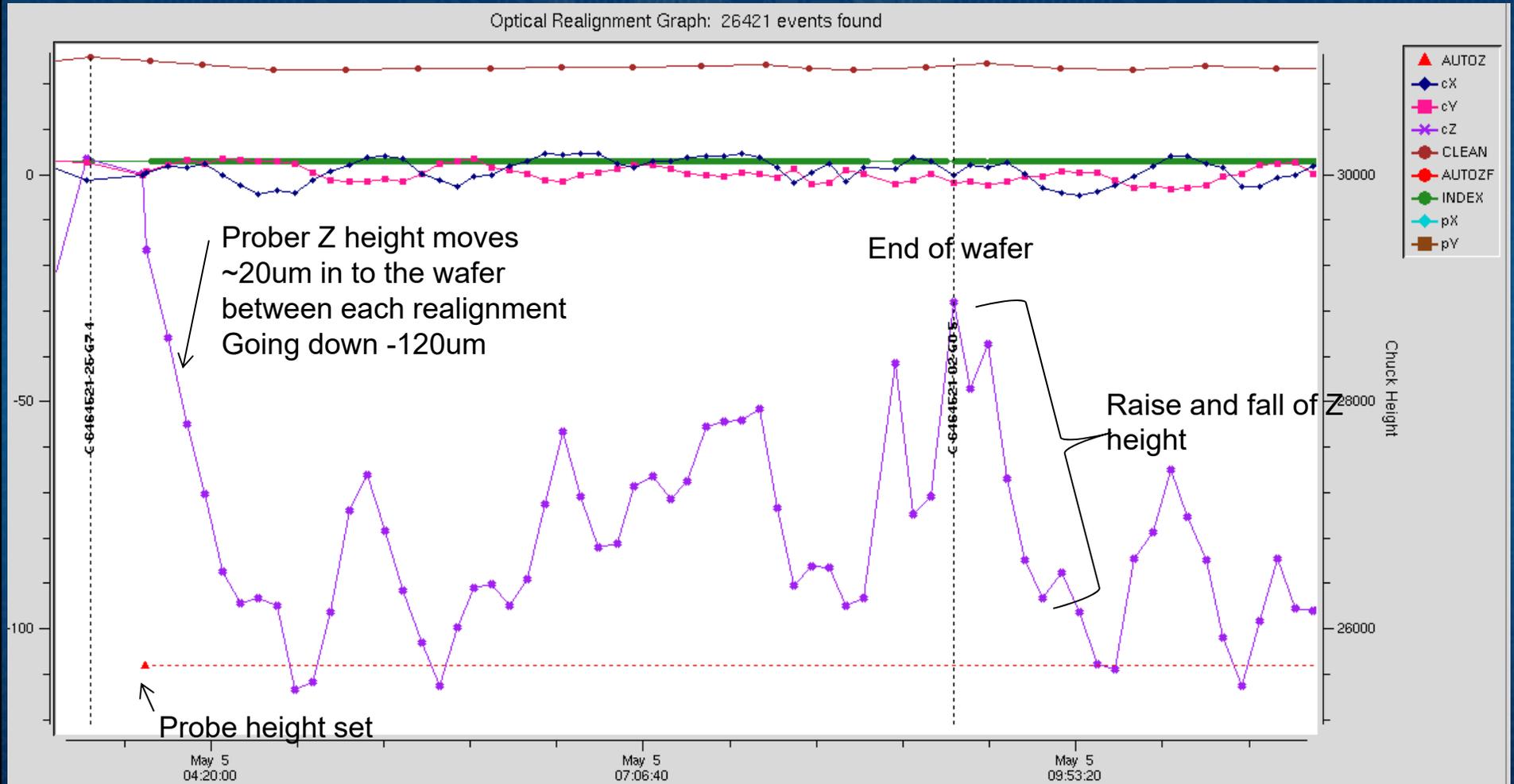
# Thermal Challenges

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# Thermal movement During probing

- Thermal movement during probing can result in unexpected added probing over travel
- Contact related issues
- Crashed probe cards

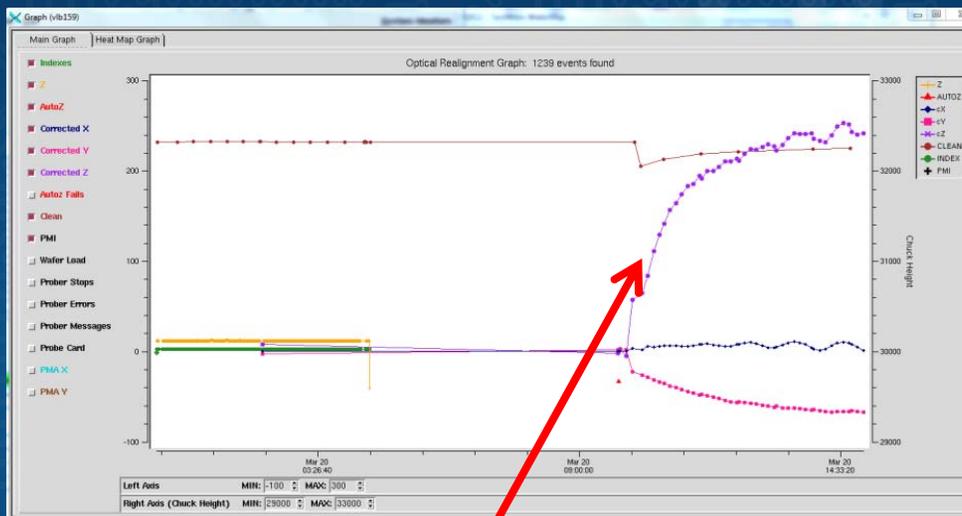
# Thermal Movement



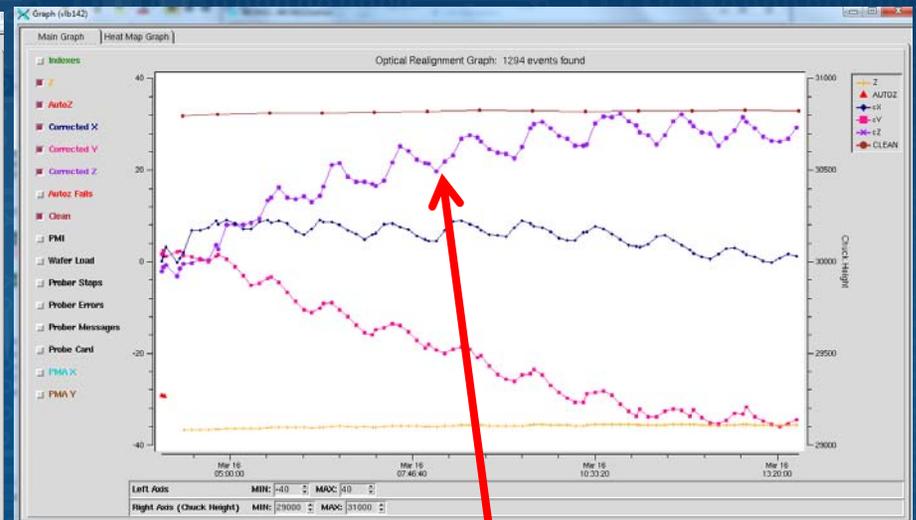
# High Temp Evaluations

## Problem

Same probe card showed different thermal curves on two different testers



**140um Z  
movement**



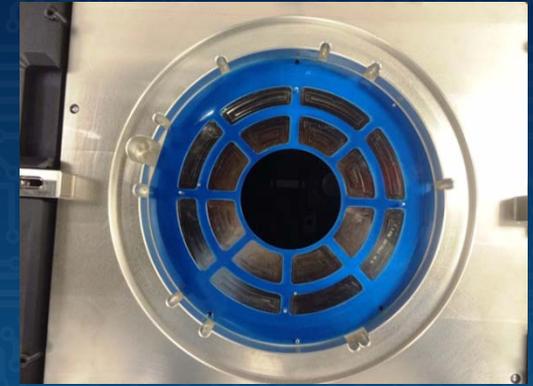
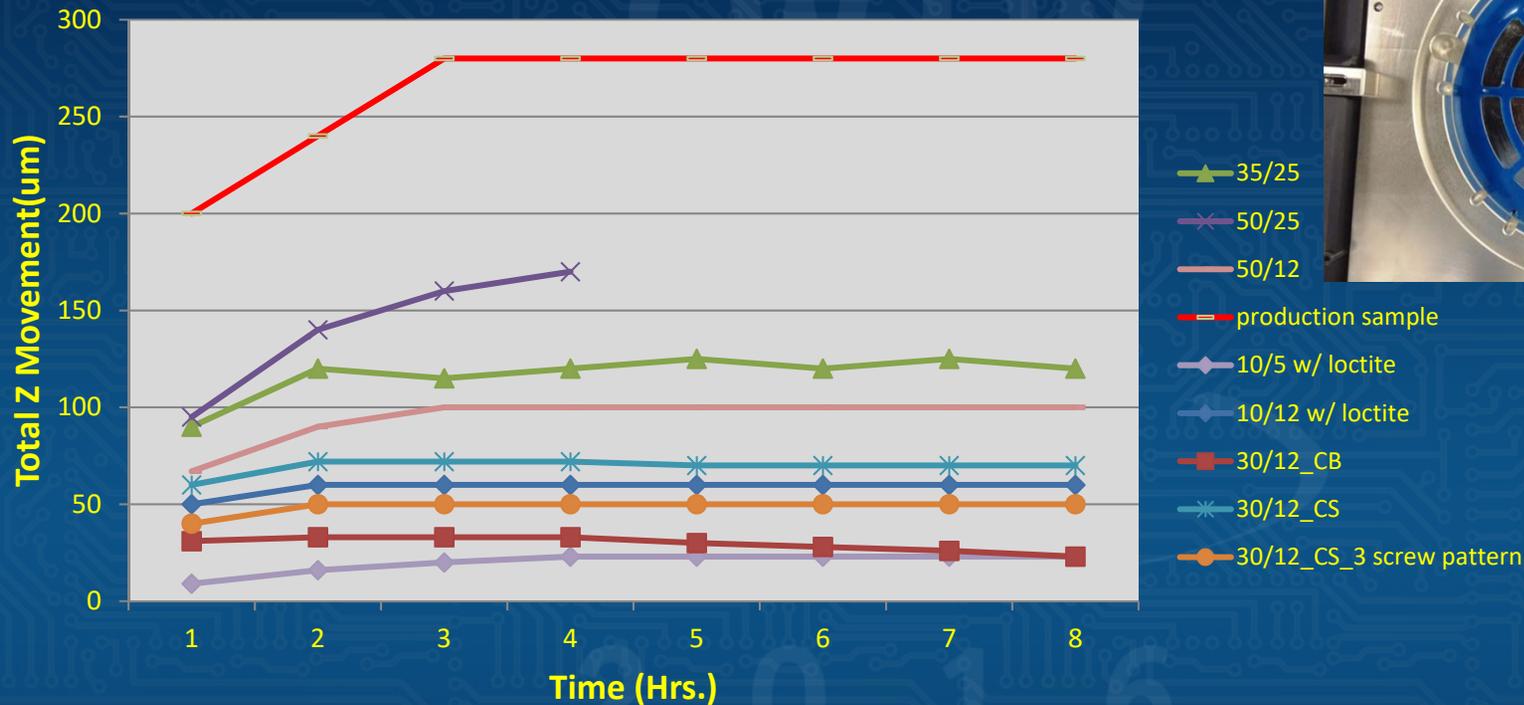
**40um Z  
movement**

**Found the probe card pan hardware was causing  
changes in thermal movement**

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# Hardware Setup Comparisons

## Hardware Setup and Torque vs. Pan Movement



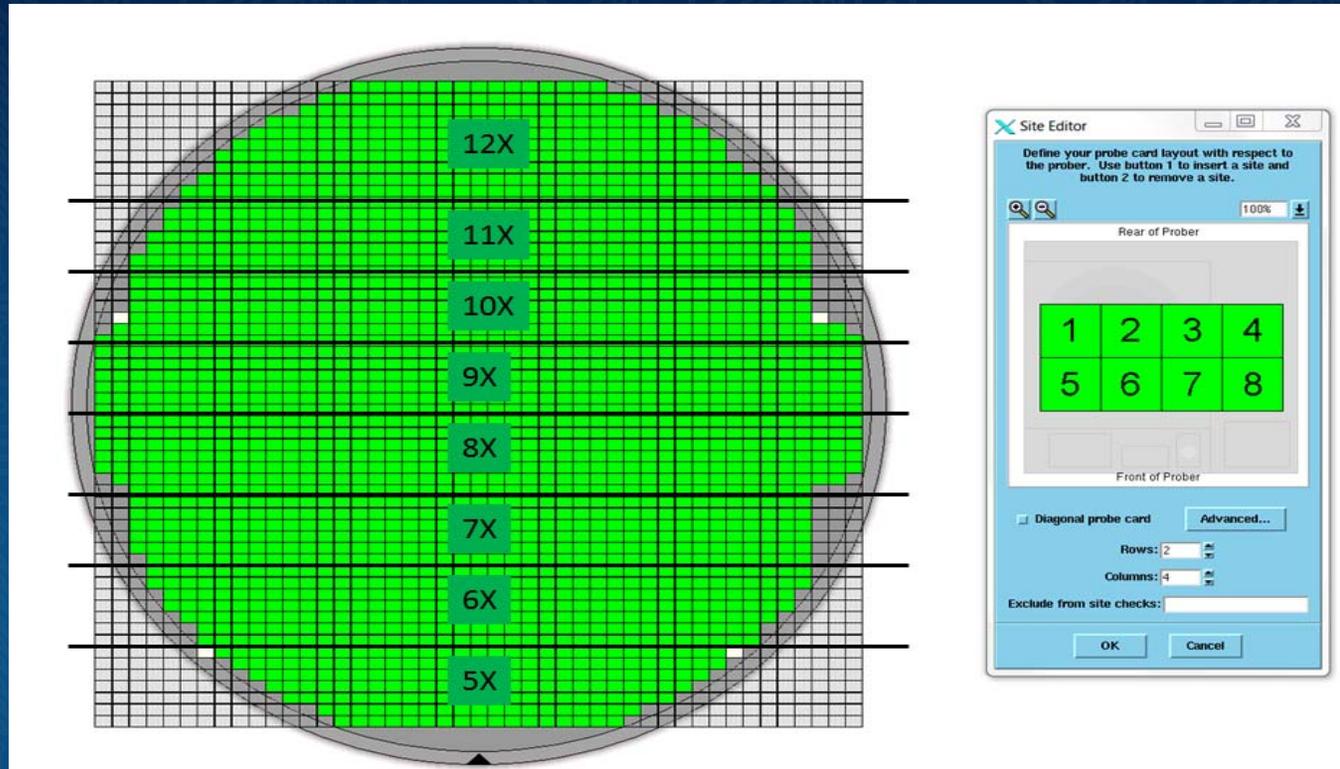
## SS and Invar Head Stage Interactions and Optimal Setup Combinations:

- 5 Screws 10 in/lbs torque with Loctite = 25um movement
- 5 Screws, 50 in/lbs torque = 40um – 50um
- 12 screws, 30 in/lbs torque = 50um movement

Top performance with all 25 screws and production acceptable= 100um

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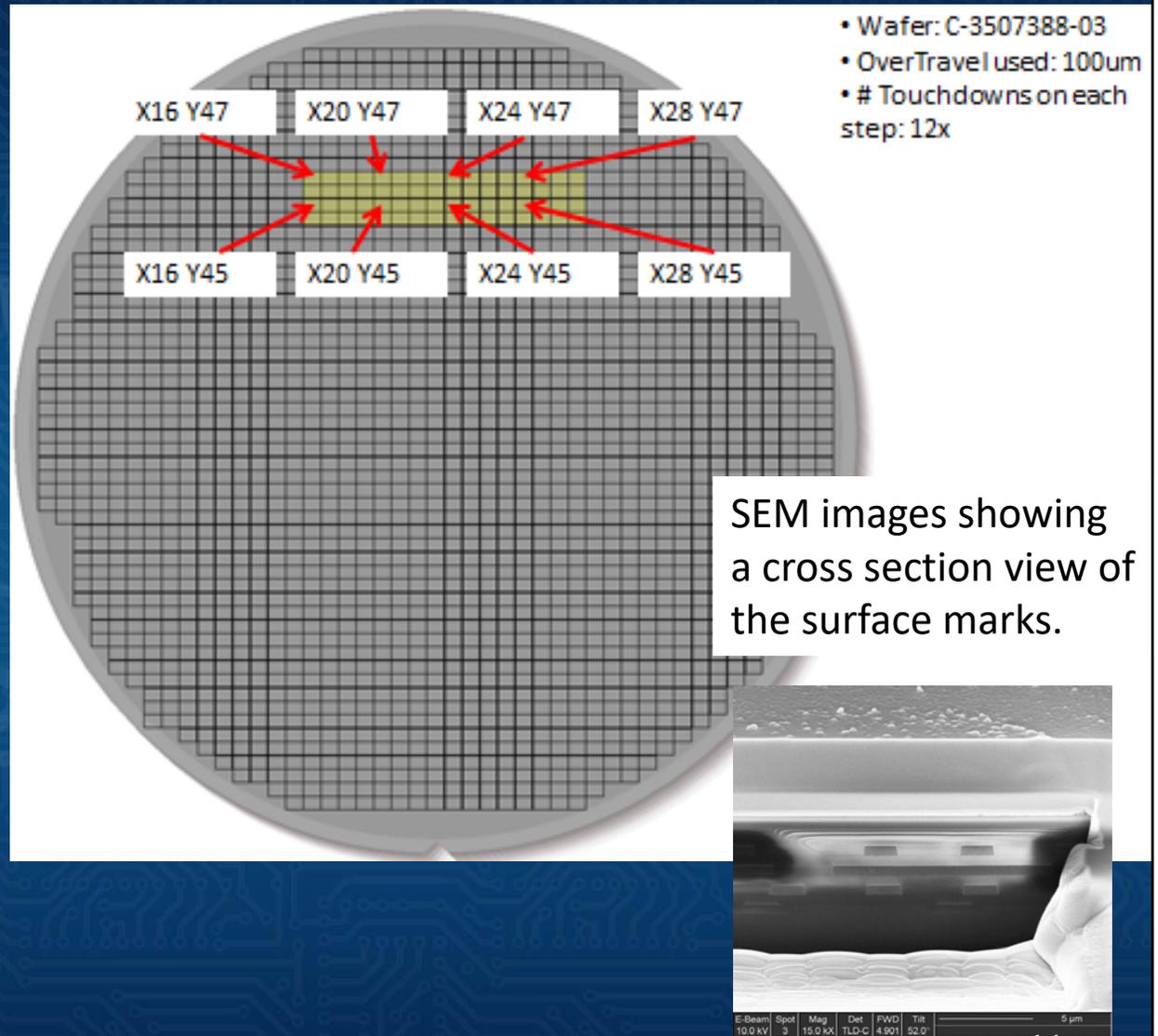
# Implications of Stepping Efficiency at Probe



- **Background:** Material baseline moved from 2 pass probe to 4 pass probe with temperature ranging from 160C to -40C.
- **Purpose:** The wafer was probed in 8 sections with a various number of touchdowns by the probe card. The objective is to determine probe process margins and what section begins to exhibit probe damage to the under layers. At what level the damage exists and to quantify the amount of damage by means of de-processing.

# Probe DOE : Results Summary

- A new wafer probed 12x with max over travel was submitted. The locations for inspection (worst case) are highlighted on the wafer map at right.
- After optical inspection, ½ of the available locations were deprocessed while retaining the pad metallization on the remaining locations.
- Optical inspection revealed marks on top of the ILD's corresponding to the probe marks.
- A FIB cross section revealed that the marks on top of the ILD's were only a surface feature, and no cracks were observed propagating downward.





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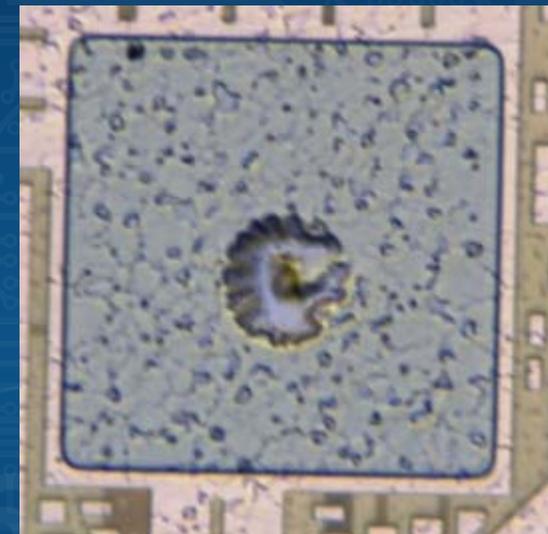
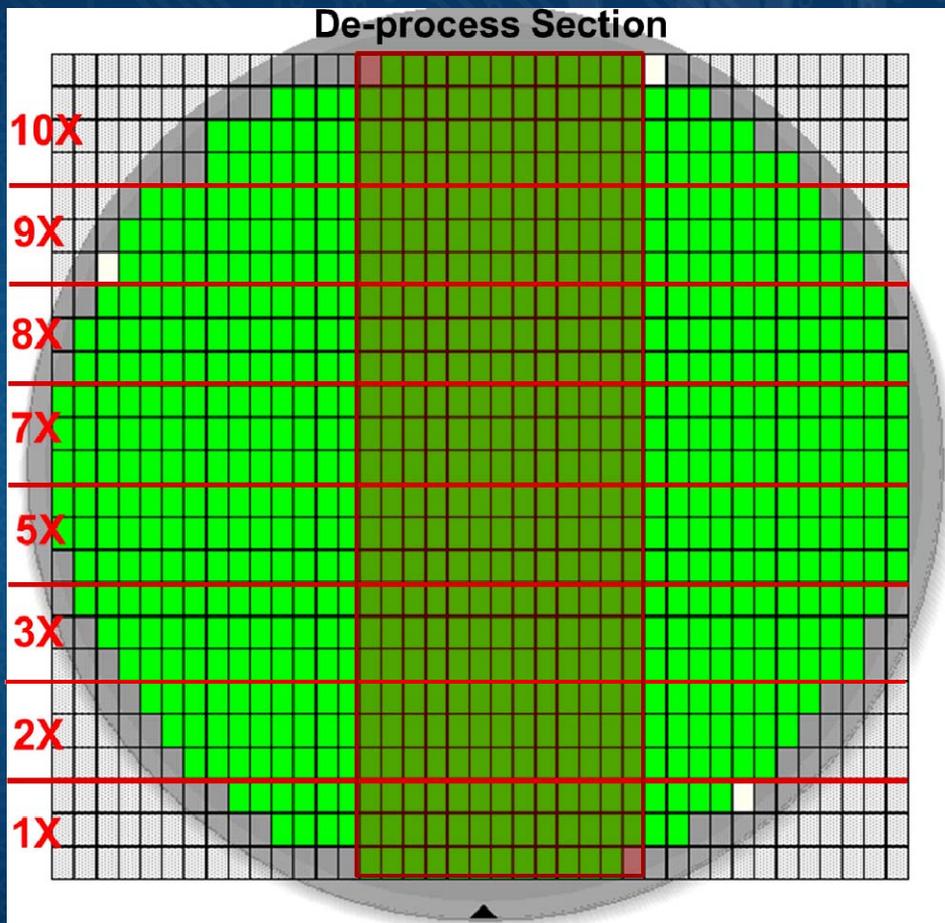
# Optimizing Z speed by PC technology

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# New Technology Development Overview

- **Problem: Base line probing can result in cracks in a new metal stack at low touchdowns.**
- **Objective: Evaluate the effect of probing on top of new stack up with a vertical probe card to reduce cracking at low touchdowns**
  - In this study two speed features were used 5Speed Variable Control.
  - 5SVC: Step one (-500um to -91um 18000um/sec 0.2G) Step two (-90um to 0um 188um/sec 0.01G)
- **Procedure: Initial visual inspection: Several probe marks were optically inspected for the appearance of the scrub marks and for any obvious damage.**
  - De-processing: Remove Pd with 1 part HCl, 10 parts Nitric Acid, 10 parts Acetic Acid (45C, 2 minutes)
  - Inspection Criteria: 16 dies per touchdown section (4 dies per site per touchdown)
- **Conclusions: No Cracks were found at 10x touchdown at 90um probing OT**

# Base line Cracking Results



5X Touchdowns

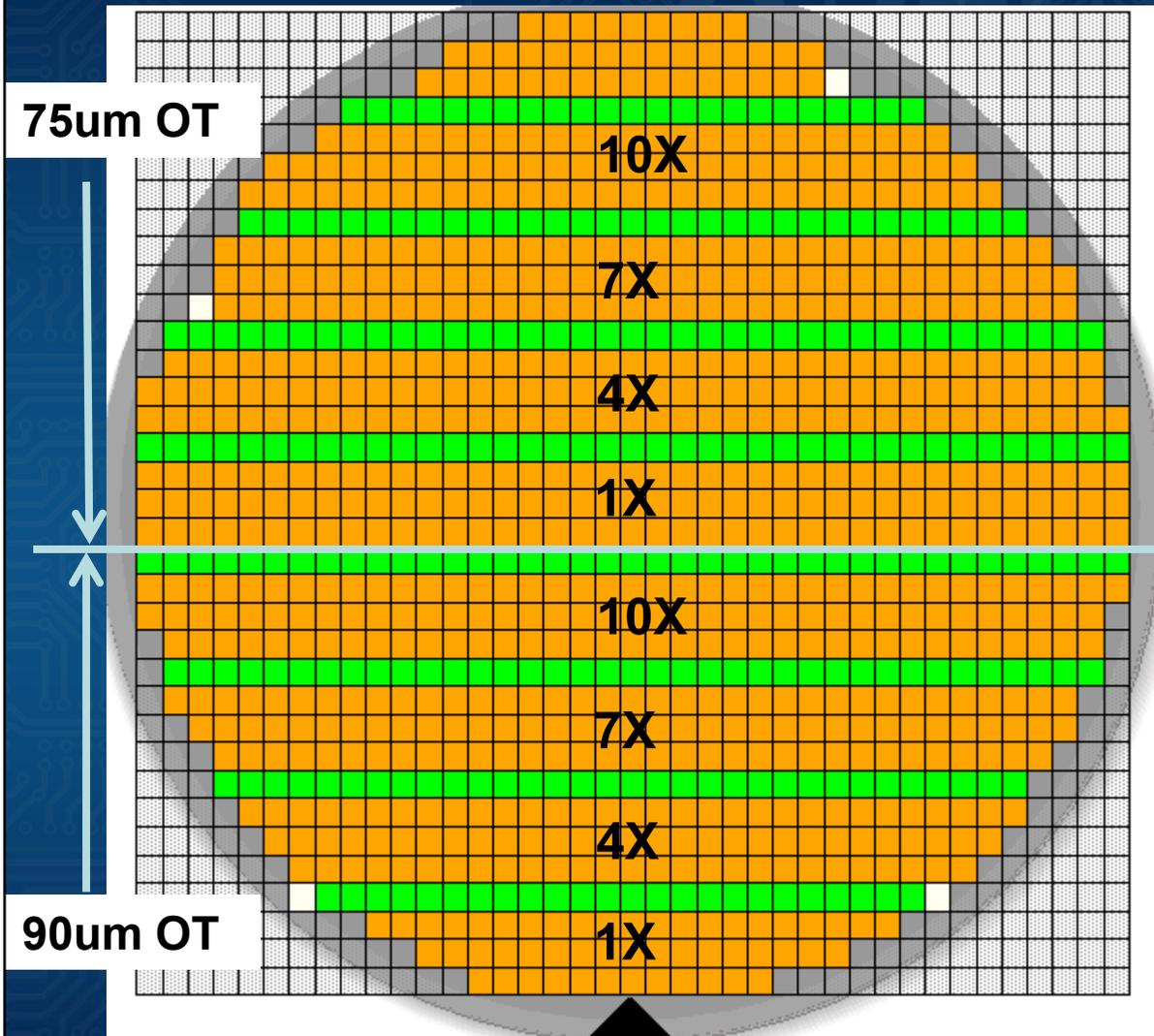
# Prober Speed Model

Probe Head

Distance: -500um to -91um  
Speed: 18000um per sec  
Acceleration 0.2G

Distance: -90um to -0um  
Speed: 188um per sec  
Acceleration 0.01G

# Probe Plan



**Probe Study Info:**

**Probe Technology:** 3mil

**DUT Count:** x2

**Number of Probes:**

**Probing Over Travel:** 75um and 90um  
on first touch 5SVC

**Planarity:** 12um

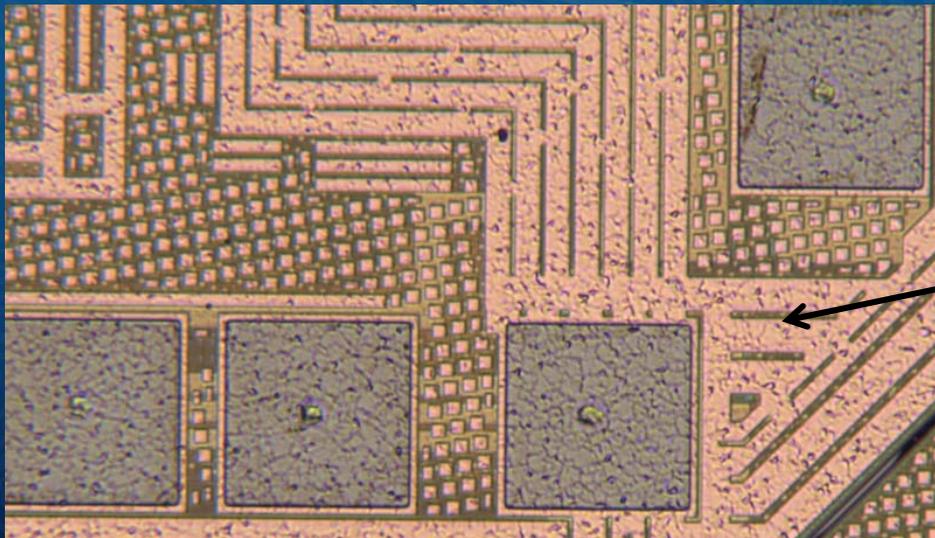
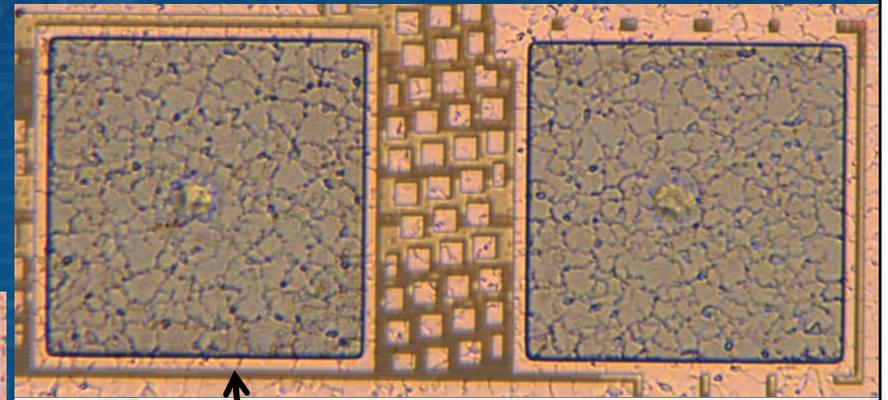
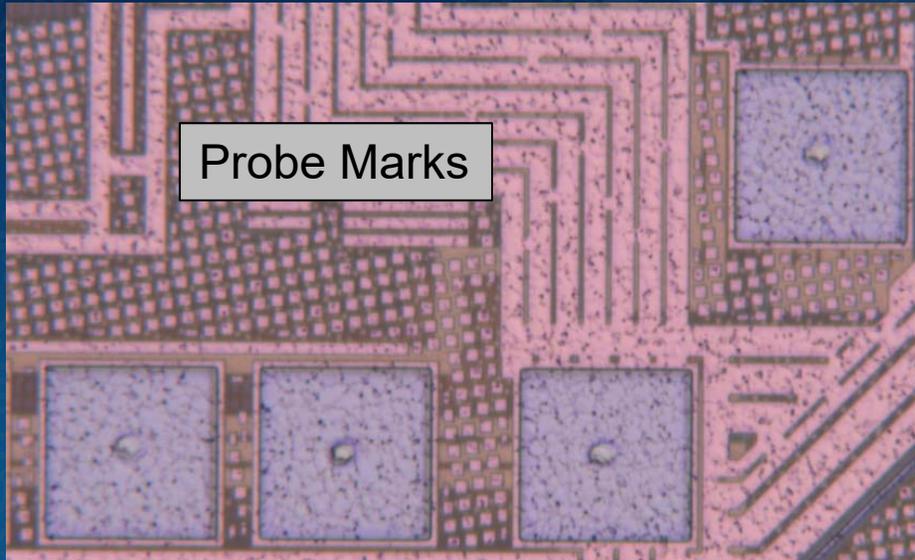
**Cleaning Interval:** 40/8

**Cleaning Over-travel:** 65um on all  
touch

**Cleaning Media:** PP150

# 5SVC Probe Results

90um OT 10x Touchdowns



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# Providing an automated probe solution

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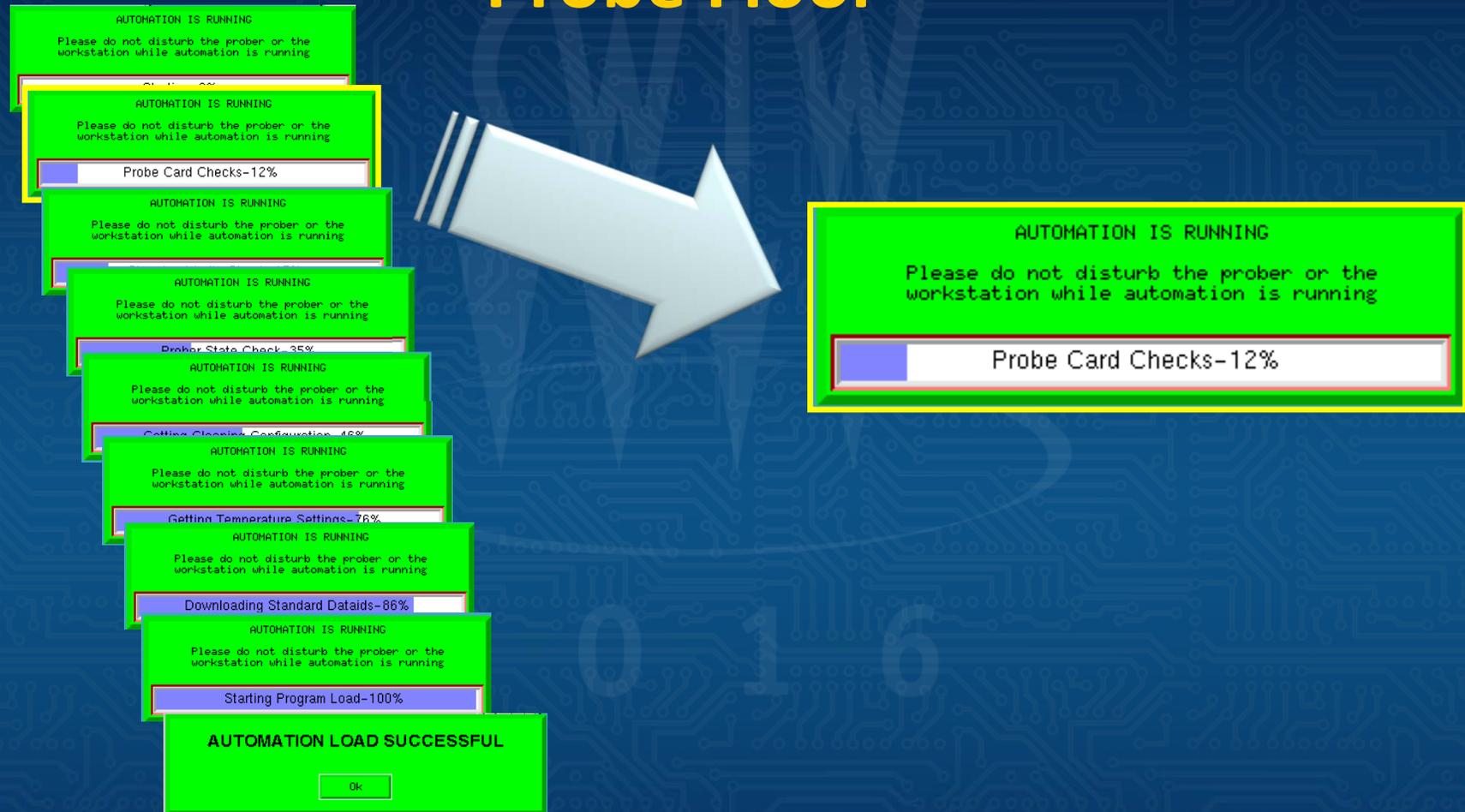
# Prober Update Procedure for 5SVC

The procedure consists of four main steps shown in the screenshots:

- UTILITY MENU:** The 'UTILITY' menu is displayed. The 'SYSTEM RESET' option is highlighted with a red circle.
- OPERATION MODE:** The 'OPERATION MODE: SYSTEM' screen is shown. A 'SYSTEM MODE CHANGE' button is highlighted with a red circle.
- PROBER CONFIGURATION DATA SETTINGS:** The 'PROBER CONFIGURATION DATA SETTINGS' menu is displayed. The 'NEEDLE CONTACT SPEED SETTINGS' option is highlighted with a red circle.
- NEEDLE CONTACT SPEED SETTINGS:** The 'NEEDLE CONTACT SPEED SETTINGS' screen is shown. The 'Needle Contact Speed (Low)' option is highlighted with a red circle.

Each screenshot includes a status bar at the top with the following information: PROBING, Z UP, ONLINE, Now temp: 114.9deg, Set temp: 140deg, Ver. S6.25.15, JAN/05/2015 23:37. The bottom of each screenshot features a row of control buttons: SYSTEM MODE CHANGE, PREVIOUS MENU, PREVIOUS PAGE, NEXT PAGE, and EXIT.

# Automated Solutions for a Production Probe Floor



- By specifying the probe card technology within production automation scripts the prober speed profiles can be optimized for production needs .



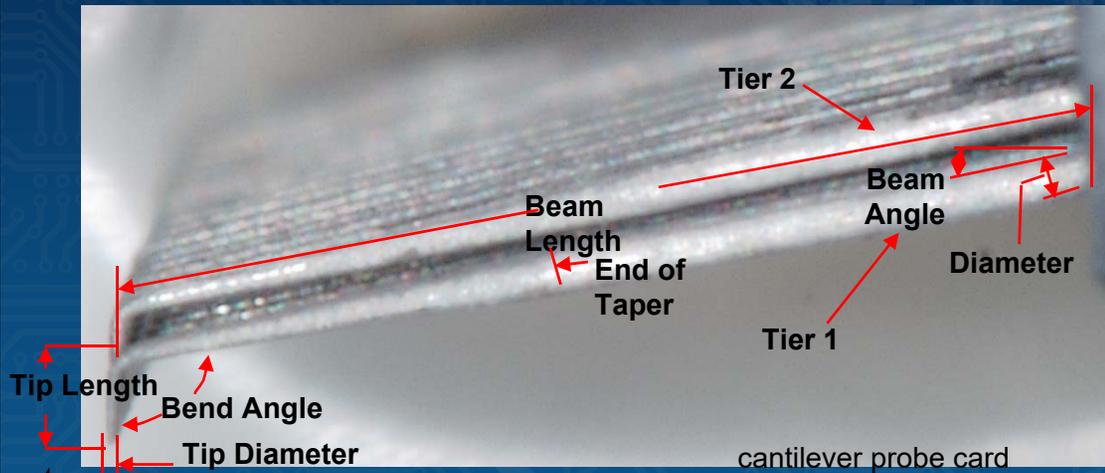
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# PC Technology Challenges

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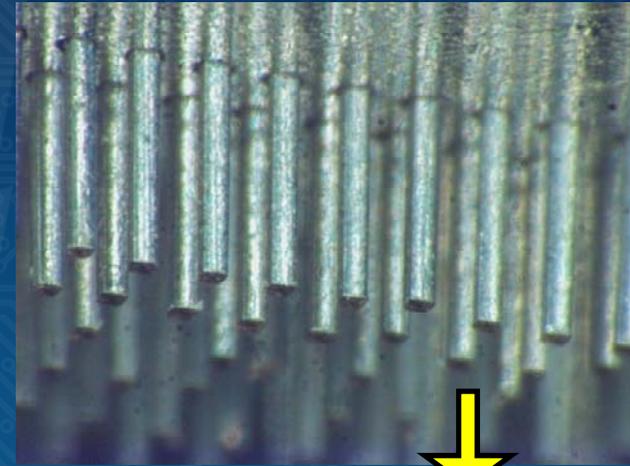
# Probe Technology

## Cantilever

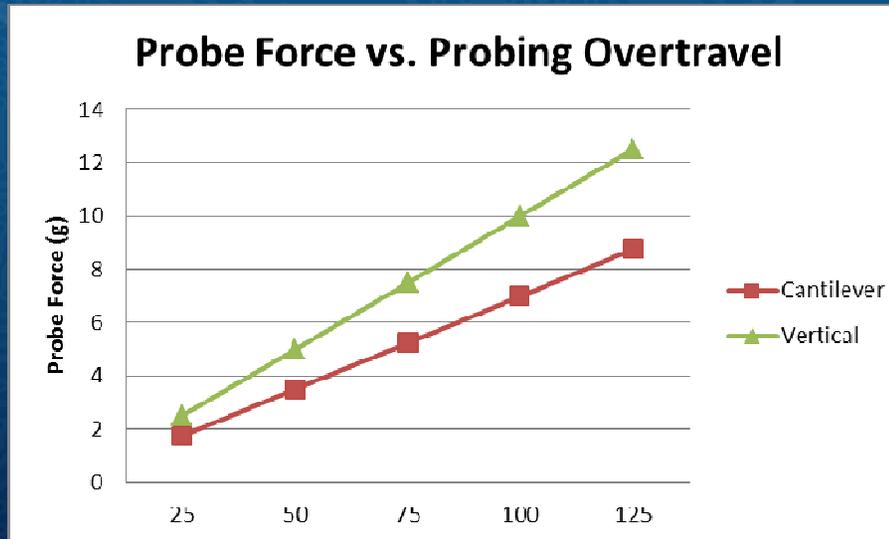


Downward and lateral force

## Vertical



Downward force only



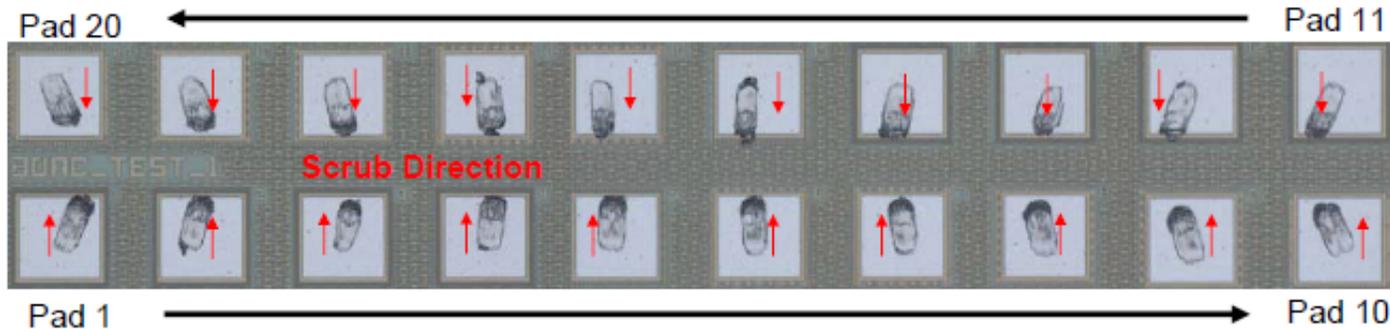


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# **Silicon Design Rules for Optimized Probe Performance**

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# Test Chip Cracking Study

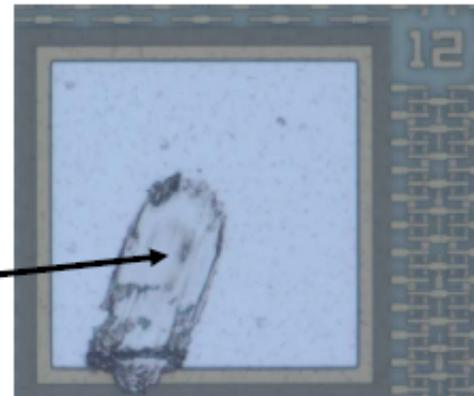


Test chip has different metal thickness and line and space designs under the probe pad

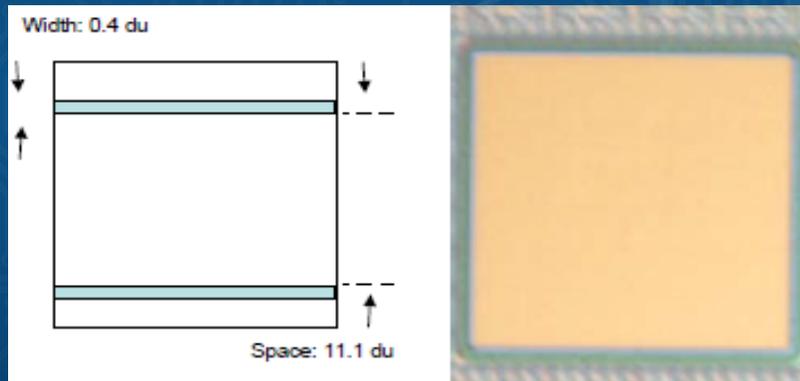
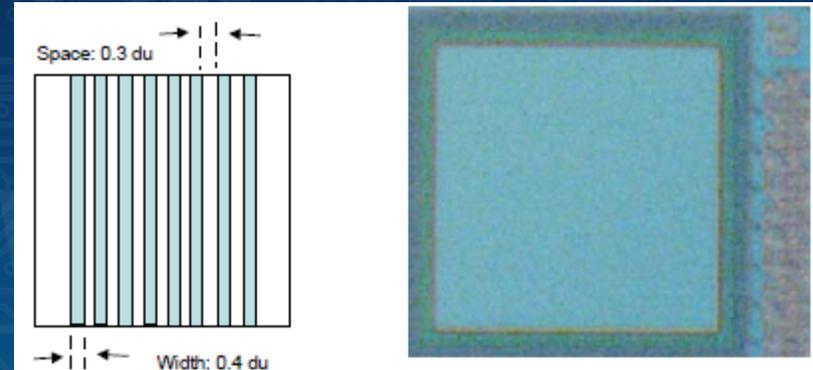
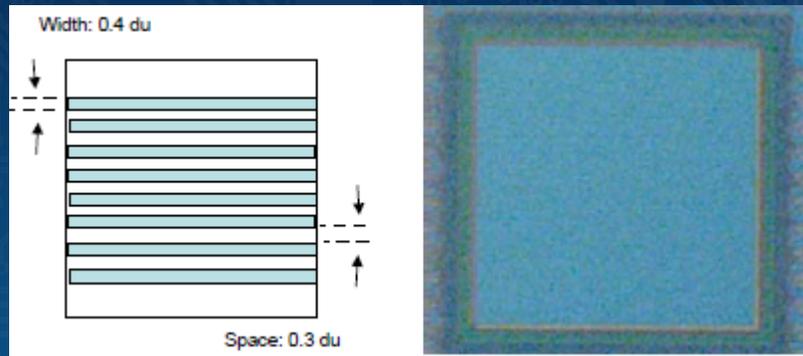
**Probed 6x touchdowns in the same location at 75um of over-travel**

Probe marks sliding off the pad

Under layer punch through

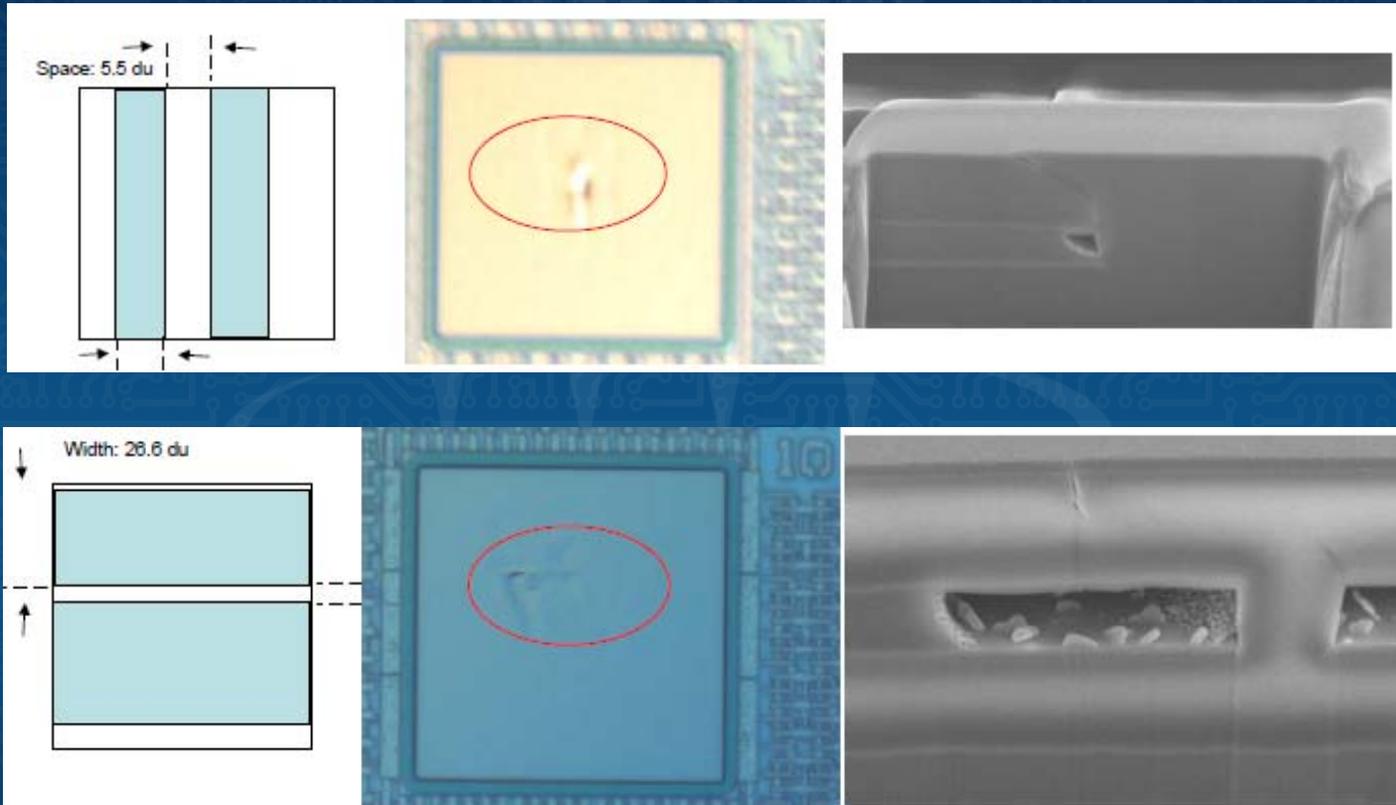


# Robust Under-layer Metal design



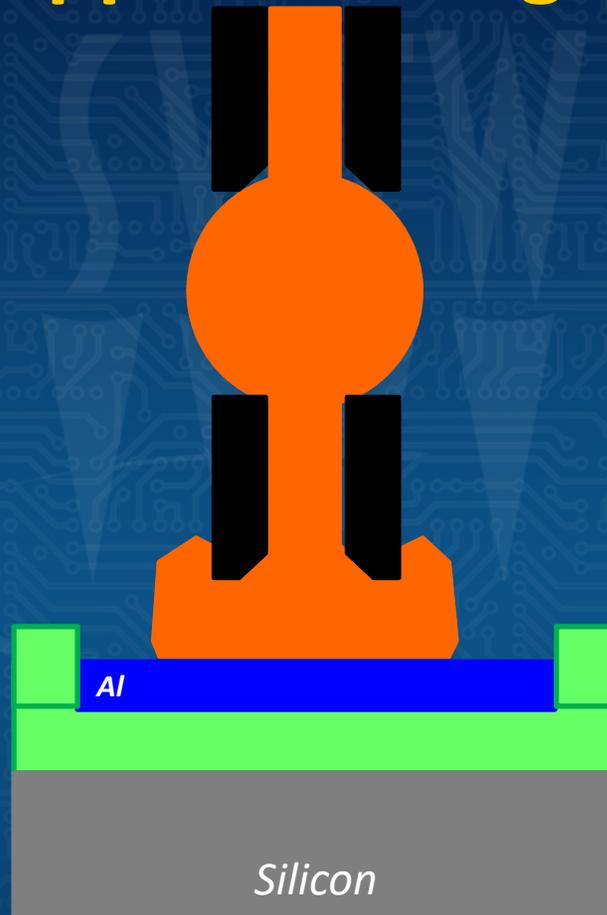
**Thin line and space does not result in cracks.  
Best performance occurs when probing in the direction of the trace lines**

# Poor Performing Metal Designs

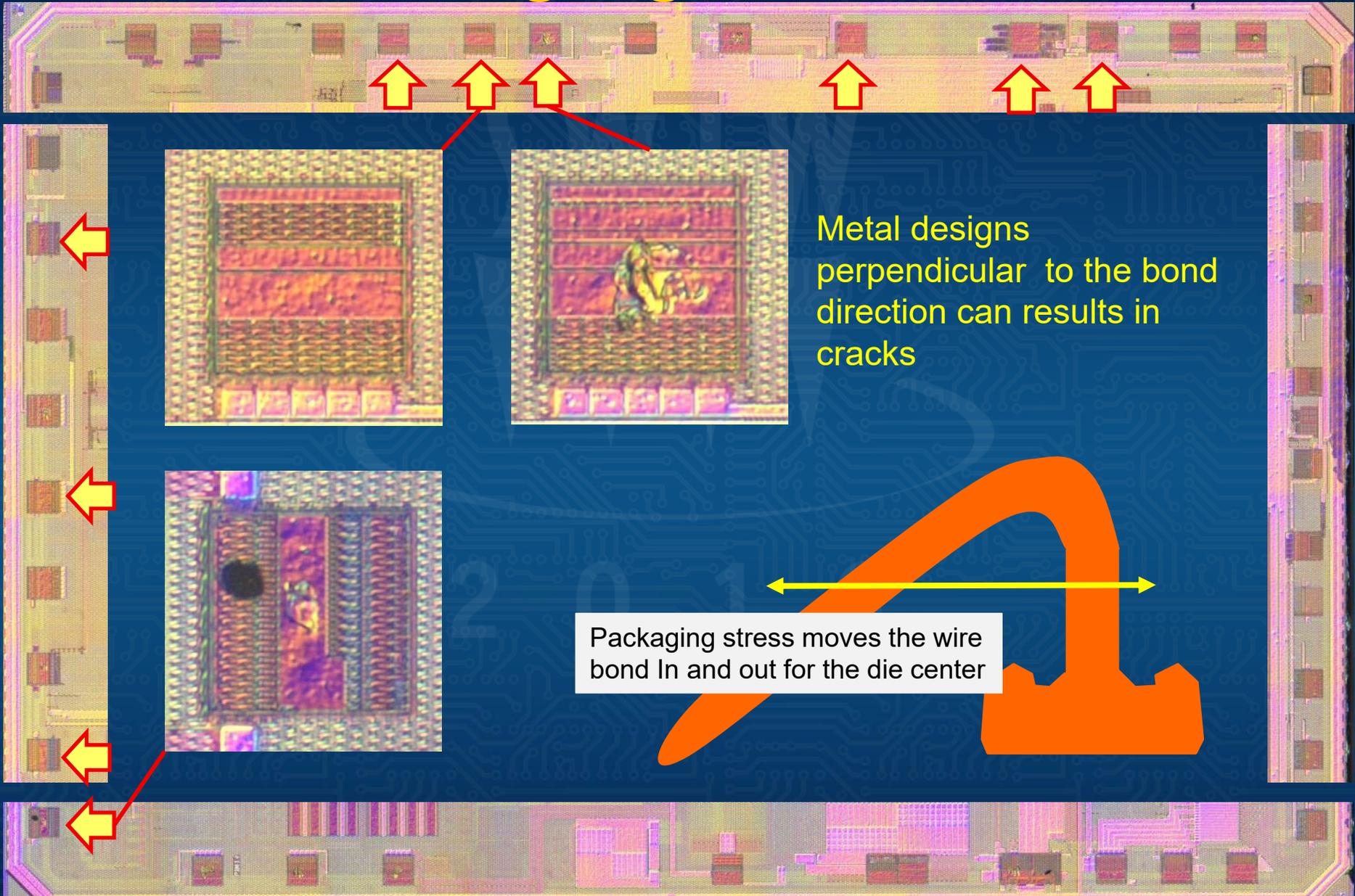


**Different material elasticity between glass and metal results in a crack in the glass when wide metal traces are used**

# What happens during bonding?



# Designing for Probe

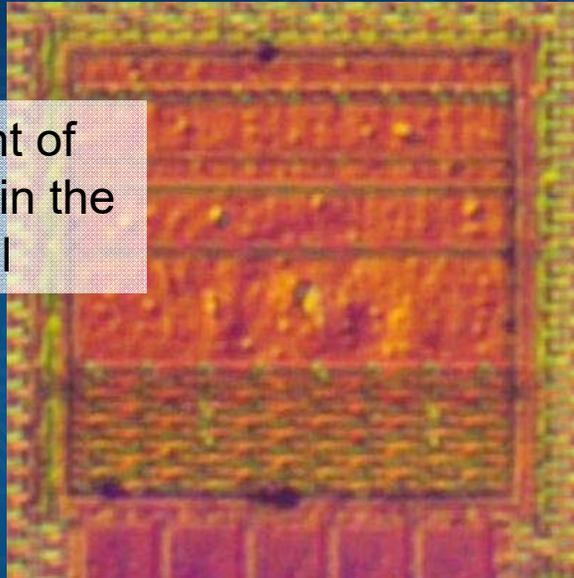


Metal designs perpendicular to the bond direction can results in cracks

Packaging stress moves the wire bond In and out for the die center

# Probe Stress

Embossment of probe mark in the barrier metal



**Pad that is probed and not bonded**

Bond crack originating at the probe mark embossment



**Pad that is probed and bonded**

# Summary of Findings

## What do we know:

- **Thermal movement needs to be addressed and can add probing over travel that is unintentional**
- **Optimized touchdown speed can affect ILD cracking**
- **PC technology**
  - Thermal compensation for at temperature probing.
  - Optimization of prober performance and identification of prober deficiencies.
  - Solutions for high pin count / low force needed
- **End solution is Si design**
  - Design for robust stack up build a higher quality IC for production use

## What is still to come:

- **Design in quality and minimize probe damage for our customers.**

# Acknowledgements

- **Connie Smith**
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- **Brennan Tran**
- **Thomas Vaughan**
- **Al Griffin**

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